

# NNCI Computation

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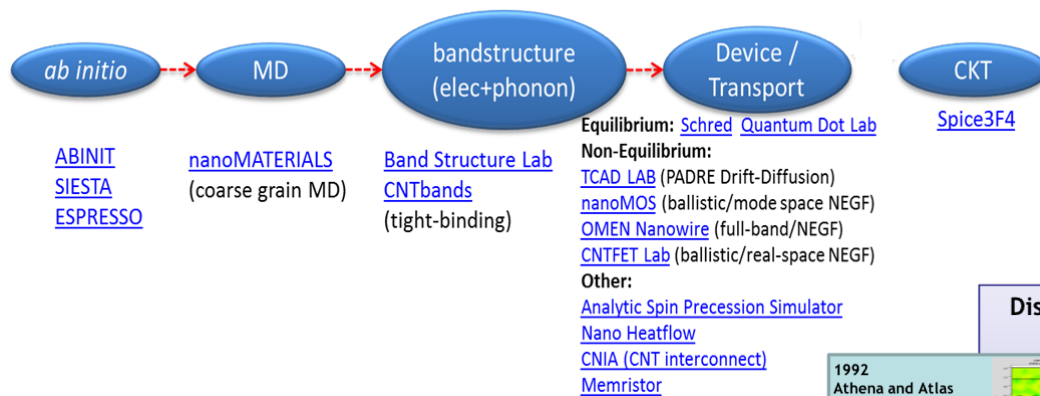
# Objectives

- To facilitate access to the modeling and simulation capabilities and expertise
- To promote and facilitate the development of the new capabilities.
- To promote utilization of the computation resources.

<https://www.nnci.net/computation-resources>

# nanoHUB.org and Silvaco Victory as a Backend

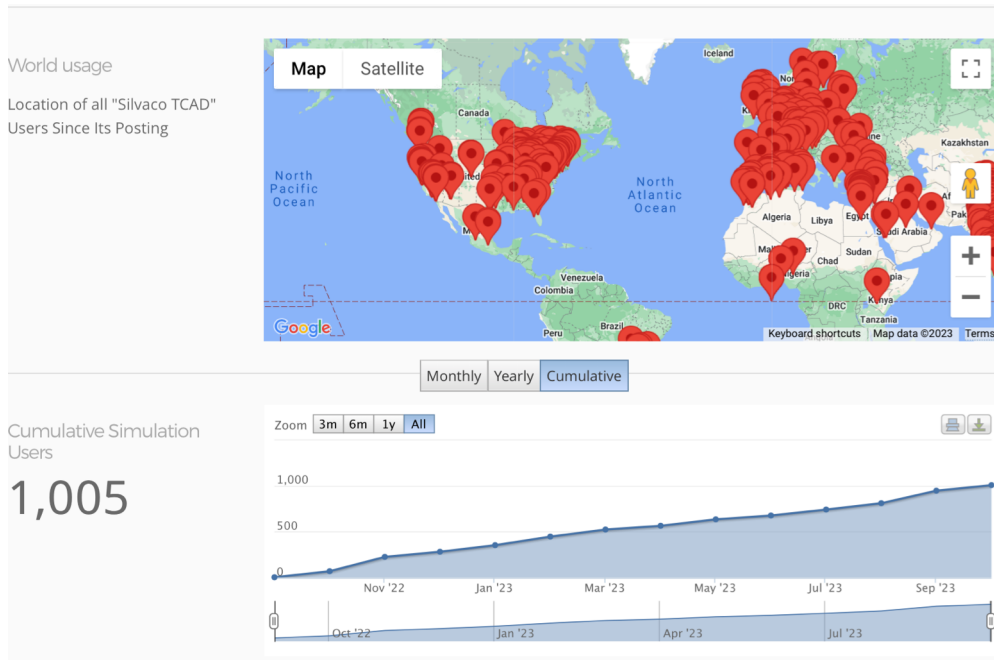
## nanoHUB Modeling Tools



## Silvaco Modeling Tools

	Display	Power	Memory	Optical	CMOS	Adv. CMOS
<b>1992</b> <b>Athena and Atlas</b> Stanford based 2D process and device sim.						
<b>1995</b> <b>Clever</b> In-House 3D field solver RC extraction						
<b>2005</b> <b>Victory Products</b> In-House 2D and 3D process and device sim.						
<b>2019</b> <b>Victory Atomistic</b> Purdue-based quantum transport solution						

# Silvaco TCAD Tool Usage



National Nanotechnology Coordinated Infrastructure

## NNCI Computation Webinar

August 23, 2023 | 4:00 p.m. - 5:00 p.m. ET



## Silvaco Technology CAD, Background, Overview, and Future

Eric Guichard | SVP and GM of TCAD, Silvaco, Inc.

**Abstract:** As one of only a few generic TCAD providers, Silvaco TCAD simulation solution covers the full spectrum, from circuit simulation size, using Victory TCAD, to nanometric size using Victory Atomistic, an NEGF-based quantum transport simulation solution inherited from Purdue University. The addition of Machine Learning and AI, to process significantly more data than before, combined with compute power and parallelization, offers the best-in-class TCAD simulation solution today. We will start this webinar with a brief introduction of the Silvaco company then discuss TCAD background (What is TCAD?, Why use TCAD?, and Challenges) then review the Silvaco TCAD solution with application examples in market segments of Power, Display, and CMOS before concluding with a discussion around AI and Digital twin.

# Short Course on Device Modeling and Simulation

## Semiconductor Device Modeling and Simulation

Dragica Vasileska  
Arizona State University



National Nanotechnology Coordinated Infrastructure

## Outline of the Short Course

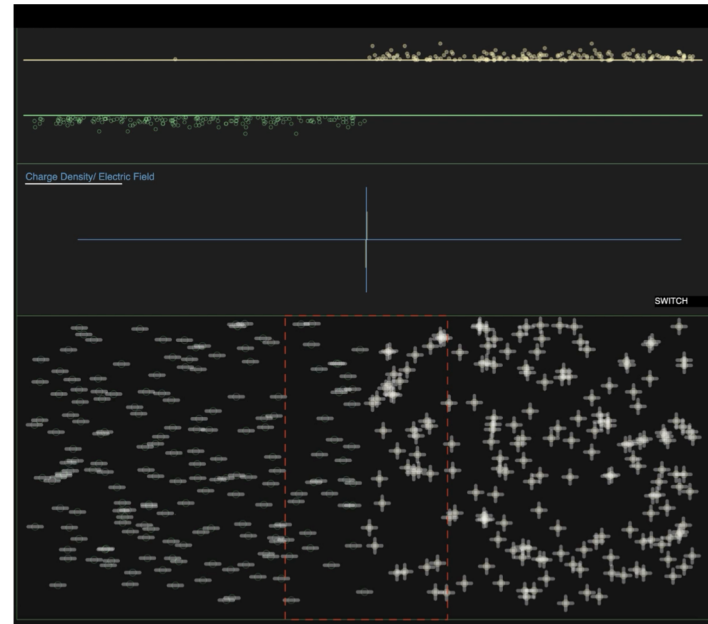
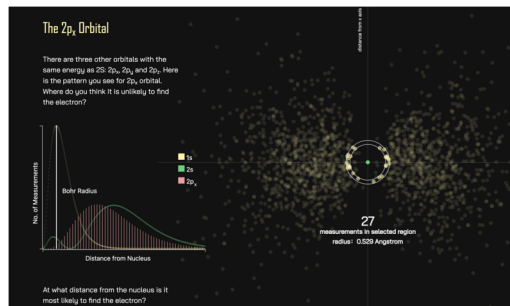
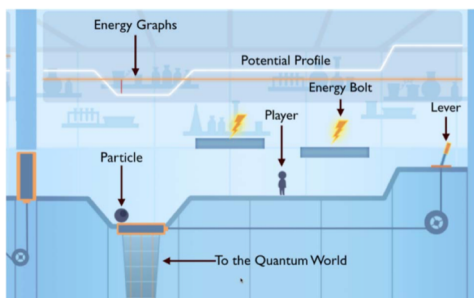
- **Computational Electronics**
- Crystallography and Bandstructure
- Semiconductor Transport Models
  - Drift-Diffusion Modeling
  - Hydrodynamic and Energy Balance Model
- Introduction to Silvaco Atlas (Device Simulation)
- Use of Silvaco's Victory Device (ATLAS) to Model Devices
  - Classical Device Modeling
    - MOS Capacitors
    - MOSFETs
    - SOI Devices
  - Introduction of Quantum-Correction Modeling
  - Modeling of Self-Heating Effects in Nanos

*Basic Knowledge Required for Semico*

# Short Course is in Production Stage!

The screenshot displays the Silvaco software interface. At the top, a window titled 'DeckBuild - 5.2.14.R - /home/manohub/vasileska/SILVACOTCAD - MOSFET\_Example1.in' shows a list of simulation tasks: 'Generate Transfer Characteristics of a MOSFET', 'Threshold Voltage and Subthreshold Slope Calculation', and 'nsubvt 0.0720817 (# 83)'. Below this, a 'Go victoryd' window shows simulation parameters: 'mesh space.mult=1.0', 'set sd\_length = 0.1', 'set channel\_length = 0.2', 'set gate\_oxide = -0.002', 'set sd\_film = 0.02', 'set BULK\_Si = 0.1', and 'set sd\_doping = 1e20'. A 'Tonyplot' window shows a 2D plot of 'Drain Current (A)' versus 'Gate Voltage (V)'. The plot shows two curves: a red curve for 'Drain Current (A)' and a green curve for 'IdVg\_1.log'. The x-axis ranges from 0 to 2, and the y-axis ranges from -10 to 2. A text box at the bottom right of the screenshot contains the URL: <https://nanohub.org/tols/silvacotcad>

# Immersive Virtual Worlds for Experiential Learning of Microelectronics



Immersive Games from Classic to Quantum Worlds

Interactive Visualizations from Hydrogen Atom to Carrier Statistics in Si

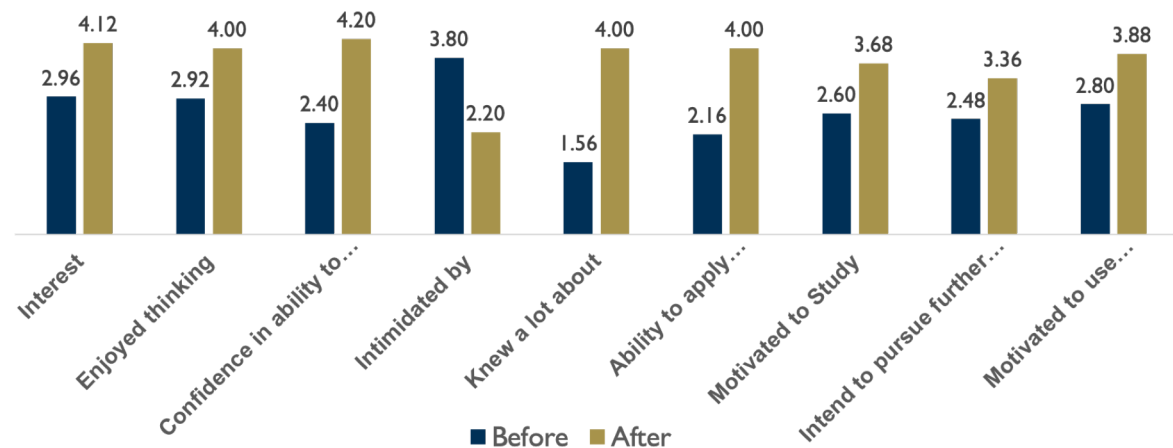
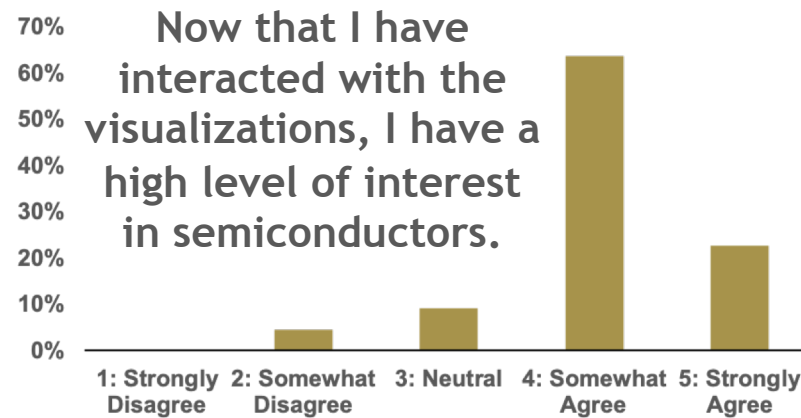
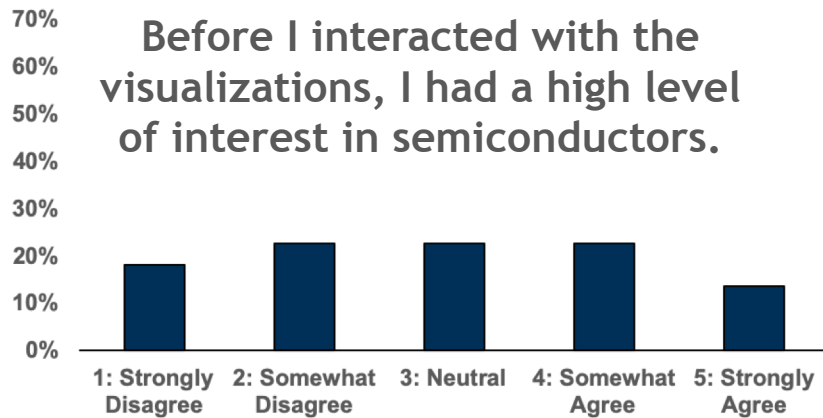
Interactive Visualizations and Virtual Reality for Semiconductor Devices (Under Development)



<https://learnqm.gatech.edu>

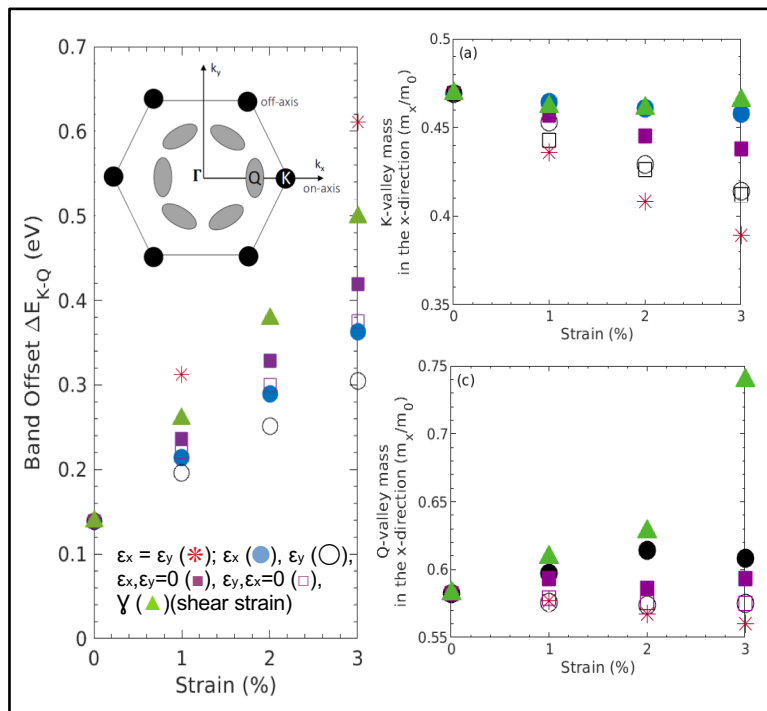


# Significant Improvement in Students' Attitude

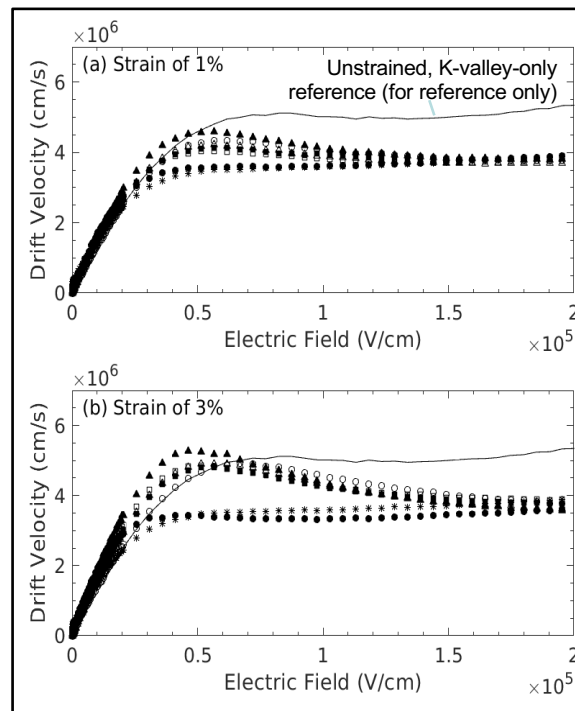


# DFT Band Structure + Semiclassical Monte Carlo Based Study of Transport in Stained MoS<sub>2</sub>

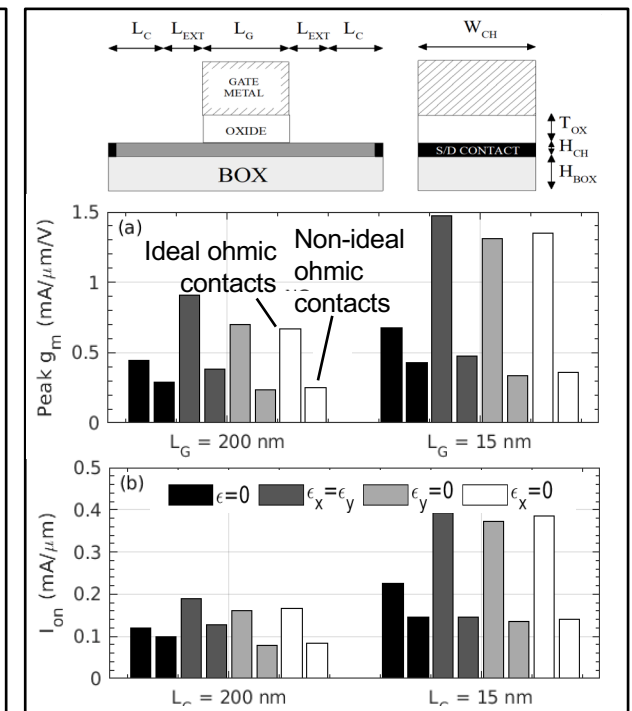
## band structure



## (2D) bulk transport



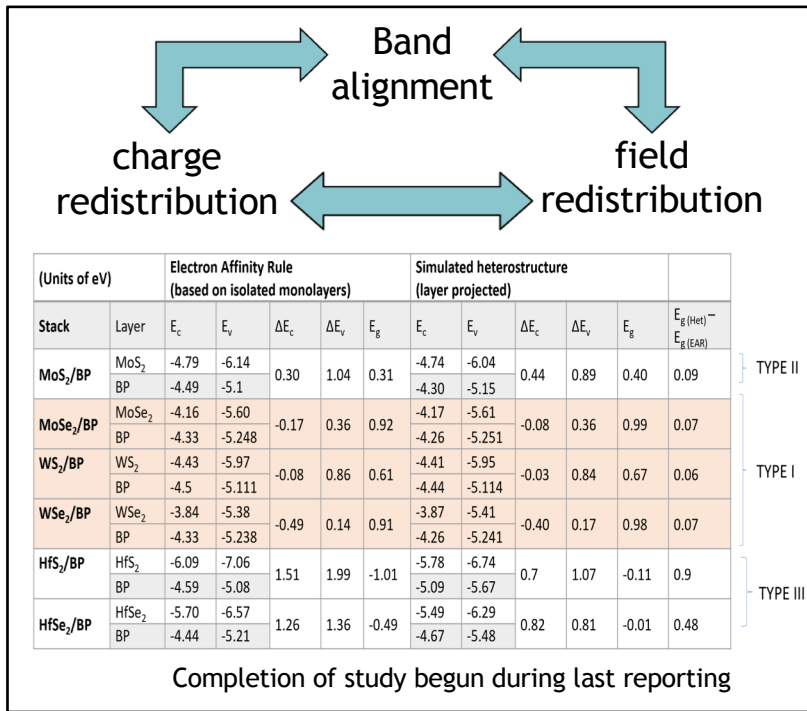
## device performance



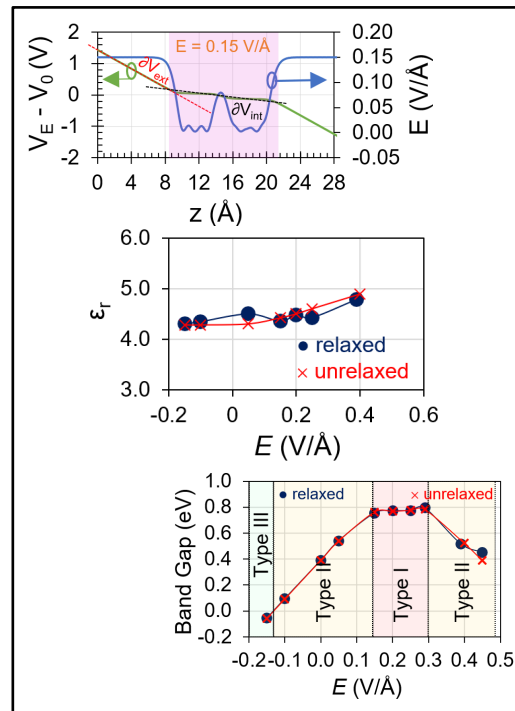


# Band Alignments in Equilibrium and under Externally Applied Electric Field and Strain

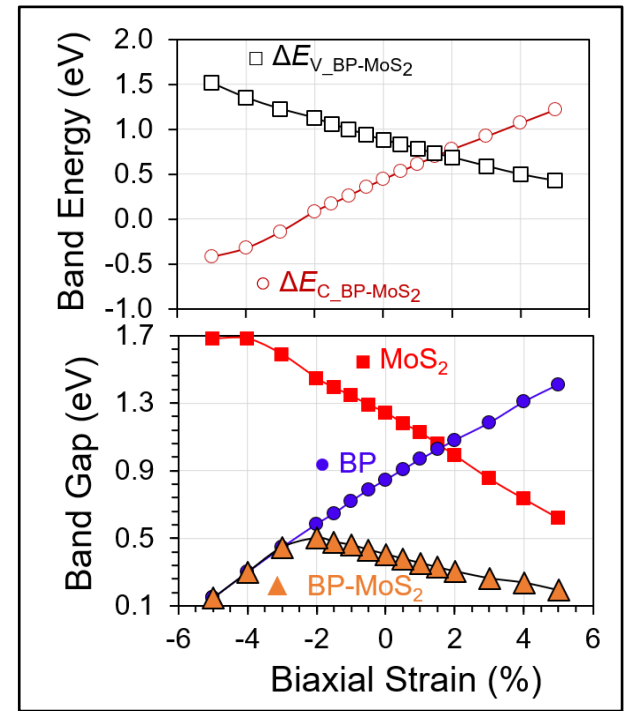
band alignment: BP/ various TMDs



BP/MoS<sub>2</sub> + electric field



BP/MoS<sub>2</sub> + strain

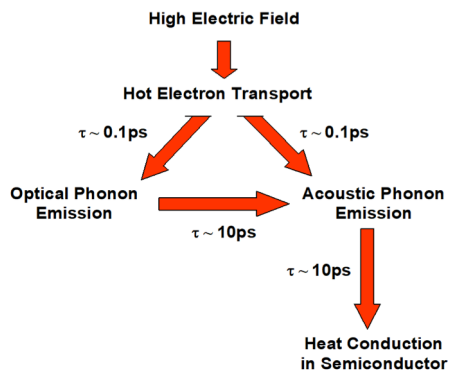


# Modeling Self-Heating in Nanoscale Devices

$$\left(\frac{\partial}{\partial t} + v_e(k) \cdot \nabla_r + \frac{e}{\hbar} E(r) \cdot \nabla_k\right) f = \sum_q \left\{ W_{e,q}^{k+q \rightarrow k} + W_{a,-q}^{k+q \rightarrow k} - W_{e,-q}^{k \rightarrow k+q} - W_{a,q}^{k \rightarrow k+q} \right\}$$

$$\left(\frac{\partial}{\partial t} + v_p(q) \cdot \nabla_r\right) g = \sum_k \left\{ W_{e,q}^{k+q \rightarrow k} - W_{a,q}^{k \rightarrow k+q} \right\} + \left(\frac{\partial g}{\partial t}\right)_{p-p}$$

**ASU Approach:**  
Energy Balance Model [1,2]

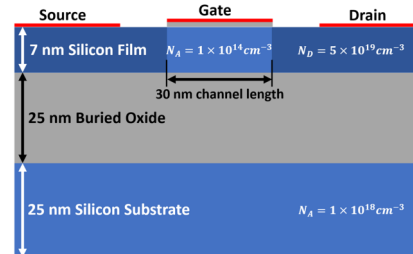


- [1] J. Lai and A. Majumdar, "Concurrent thermal and electrical modeling of submicrometer silicon devices", J. Appl. Phys., Vol. 79, 7353 (1996).  
 [2] K. Raleva, D. Vasileska, S. M. Goodnick and M. Nedjalkov, "Modeling Thermal Effects in Nanodevices", IEEE Transactions on Electron Devices, vol. 55, issue 6, pp. 1306-1316, June 2008.

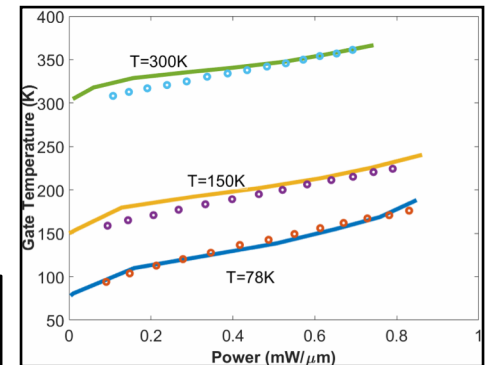
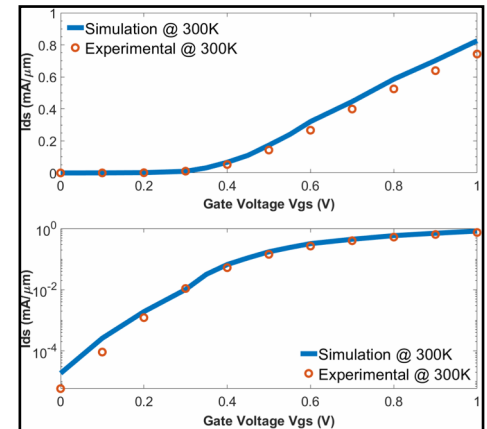
$$C_{LO} \frac{\partial T_{LO}}{\partial t} = \frac{3nk_B}{2} \left( \frac{T_e - T_L}{\tau_{e-LO}} \right) + \frac{nm * v_d^2}{2\tau_{e-LO}} - C_{LO} \left( \frac{T_{LO} - T_A}{\tau_{LO-A}} \right),$$

$$C_A \frac{\partial T_A}{\partial t} = \nabla \cdot (k_A \nabla T_A) + C_{LO} \left( \frac{T_{LO} - T_A}{\tau_{LO-A}} \right) + \frac{3nk_B}{2} \left( \frac{T_e - T_L}{\tau_{e-L}} \right).$$

Model Validation



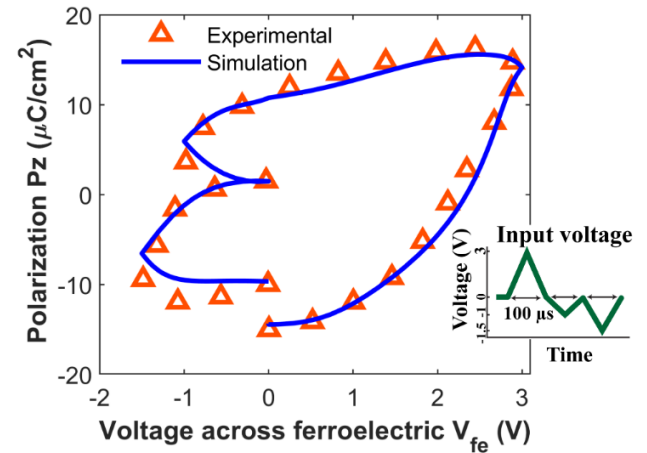
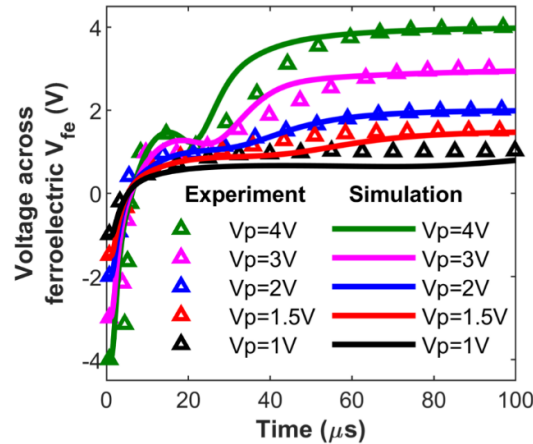
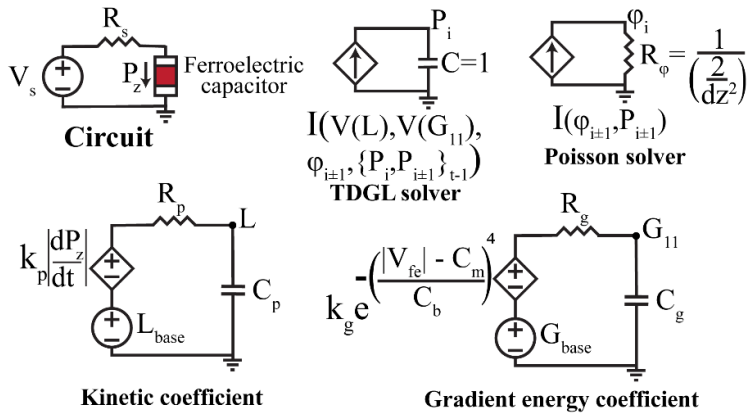
Simulation Results



**Experimental data:**

M. Casse et al., "FDSOI for cryoCMOS electronics: device characterization towards compact model", IEDM (2022)

# Ferroelectric Device Modeling Framework



**Phase-Field Based Compact Models for FE Capacitors, IEEE-T-ED 2023**

**30,000X Speed up compared to prior phase-field simulations with no loss of accuracy.**

Models to be released on nanoHub



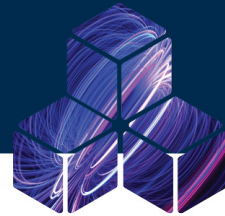
Naeemi, GT 11

# Computation Webinar Series



## NNCI Webinar

February 15, 2023 | 4:00 p.m. - 5:00 p.m. ET



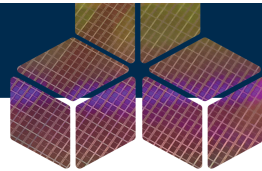
### ANTIFERROMAGNETIC TUNNEL JUNCTIONS FOR SPINTRONICS

Evgeny Tsybal | Department of Physics and Astronomy, University of Nebraska-Lincoln



## NNCI Computational Webinar

April 27, 2022 | 3PM - 4PM ET



### SEMICONDUCTOR WORKFORCE DEVELOPMENT THROUGH IMMERSIVE SIMULATIONS ON NANO HUB.ORG

Gerhard Klimeck, Tanya Faltens, Daniel Mejia, Alejandro Strachan, Lynn Zentner, Michael Zentner\*  
Network for Computational Nanotechnology, Purdue University

\*San Diego Supercomputing Center, UCSD



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### Silvaco Technology CAD, Background, Overview, and Future

Eric Guichard | SVP and GM of TCAD, Silvaco, Inc.



[https://www.youtube.com/channel/UCN1laymO8KcA\\_fMEB1FhPgQ](https://www.youtube.com/channel/UCN1laymO8KcA_fMEB1FhPgQ)

# Next Computation Webinar



## NNCI Webinar

November 16, 2023 | 3:00 p.m. - 4:00 p.m. ET



## PARTICLE BASED SIMULATION OF WEIDEBANDGAP DEVICES

Stephen Goodnick | Department of Electrical Engineering at  
Arizona State University



[https://www.youtube.com/channel/UCN1IaymO8KcA\\_fMEB1FhPgQ](https://www.youtube.com/channel/UCN1IaymO8KcA_fMEB1FhPgQ)